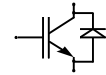


Technische Information / Technical Information

IGBT-Module
IGBT-Modules

FP15R12KE3G

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Vorläufige Daten
Preliminary data

Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Diode Gleichrichter/ Diode Rectifier

Periodische Rückw. Spitzenspernung repetitive peak reverse voltage		V_{RRM}	1600	V
Gleichrichter Ausgang Grenzeffektivstrom maximum RMS current at Rectifier output		I_{RMSmax}	60	A
Dauergleichstrom DC forward current	$T_C = 80^\circ C$	I_d	15	A
Stoßstrom Grenzwert surge forward current	$t_p = 10 \text{ ms}, T_{vj} = 25^\circ C$ $t_p = 10 \text{ ms}, T_{vj} = 150^\circ C$	I_{FSM}	315 260	A A
Grenzlastintegral I^2t - value	$t_p = 10 \text{ ms}, T_{vj} = 25^\circ C$ $t_p = 10 \text{ ms}, T_{vj} = 150^\circ C$	I^2t	500 340	A^2s A^2s

Transistor Wechselrichter/ Transistor Inverter

Kollektor-Emitter-Spernung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ C$ $T_C = 25^\circ C$	$I_{C,nom.}$ I_C	15 25	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1 \text{ ms}, T_C = 80^\circ C$	I_{CRM}	30	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ C$	P_{tot}	100	W
Gate-Emitter-Spernung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Wechselrichter/ Diode Inverter

Dauergleichstrom DC forward current	$T_C = 80^\circ C$	I_F	15	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1 \text{ ms}$	I_{FRM}	30	A
Grenzlastintegral I^2t - value	$V_R = 0V, t_p = 10\text{ms}, T_{vj} = 125^\circ C$	I^2t	60	A^2s

Transistor Brems-Chopper/ Transistor Brake-Chopper

Kollektor-Emitter-Spernung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ C$ $T_C = 25^\circ C$	$I_{C,nom.}$ I_C	10 18	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1 \text{ ms}, T_C = 80^\circ C$	I_{CRM}	20	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ C$	P_{tot}	80	W
Gate-Emitter-Spernung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Brems-Chopper/ Diode Brake-Chopper

Dauergleichstrom DC forward current	$T_C = 80^\circ C$	I_F	10	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1 \text{ ms}$	I_{FRM}	20	A

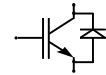
prepared by: Andreas Schulz	date of publication:10.08.2001
approved by: Robert Severin	revision: 1

Technische Information / Technical Information

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Modul Isolation/ Module Isolation

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min. NTC connected to Baseplate	V_{ISOL}	2,5	kV
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Elektrische Eigenschaften / Electrical properties

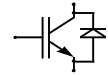
Charakteristische Werte / Characteristic values

Diode Gleichrichter/ Diode Rectifier

			min.	typ.	max.	
Durchlaßspannung forward voltage	$T_{vj} = 150^{\circ}\text{C}$, $I_F = 15\text{ A}$	V_F	-	0,95	-	V
Schleusenspannung threshold voltage	$T_{vj} = 150^{\circ}\text{C}$	$V_{(TO)}$	-	-	0,8	V
Ersatzwiderstand slope resistance	$T_{vj} = 150^{\circ}\text{C}$	r_T	-	-	10,5	m Ω
Sperrstrom reverse current	$T_{vj} = 150^{\circ}\text{C}$, $V_R = 1600\text{ V}$	I_R	-	2	-	mA
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^{\circ}\text{C}$	R_{AA+CC}	-	5	-	m Ω

Transistor Wechselrichter/ Transistor Inverter

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 15\text{ A}$	$V_{CE\text{ sat}}$	-	1,7	2,2	V
	$V_{GE} = 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $I_C = 15\text{ A}$		-	2	-	V
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 0,5\text{ mA}$	$V_{GE(TO)}$	5,0	5,8	6,5	V
Eingangskapazität input capacitance	f = 1MHz, $T_{vj} = 25^{\circ}\text{C}$ $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{ies}	-	1,1	-	nF
Kollektor-Emitter Reststrom collector-emitter cut off current	$V_{GE} = 0\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 1200\text{ V}$	I_{CES}	-	-	5	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}	-	-	400	nA
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$	$t_{d,on}$	-	85	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$	t_r	-	30	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$	$t_{d,off}$	-	420	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$	t_f	-	65	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$ $V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$ $L_S = 45\text{ nH}$	E_{on}	-	2,1	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 600\text{ V}$ $V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 75\text{ Ohm}$ $L_S = 45\text{ nH}$	E_{off}	-	1,5	-	mWs
Kurzschlußverhalten SC Data	$t_P \leq 10\mu\text{s}$, $V_{GE} \leq 15\text{V}$, $R_G = 75\text{ Ohm}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 720\text{ V}$	I_{SC}	-	60	-	A



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Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

			min.	typ.	max.	
Modulinduktivität stray inductance module		L_{GCE}	-	-	100	nH
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^\circ\text{C}$	$R_{\text{CC}'+\text{EE}'}$	-	7	-	mΩ
Diode Wechselrichter/ Diode Inverter			min.	typ.	max.	
Durchlaßspannung forward voltage	$V_{\text{GE}} = 0\text{V}, T_{\text{vj}} = 25^\circ\text{C}, I_{\text{F}} = 15\text{ A}$ $V_{\text{GE}} = 0\text{V}, T_{\text{vj}} = 125^\circ\text{C}, I_{\text{F}} = 15\text{ A}$	V_{F}	-	1,65	2,2	V
Rückstromspitze peak reverse recovery current	$I_{\text{F}}=I_{\text{Nenn}}, -di_{\text{F}}/dt = 400\text{ A}/\mu\text{s}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 25^\circ\text{C}, V_{\text{R}} = 600\text{ V}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 125^\circ\text{C}, V_{\text{R}} = 600\text{ V}$	I_{RM}	-	16	-	A
Sperrverzögerungsladung recovered charge	$I_{\text{F}}=I_{\text{Nenn}}, -di_{\text{F}}/dt = 400\text{ A}/\mu\text{s}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 25^\circ\text{C}, V_{\text{R}} = 600\text{ V}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 125^\circ\text{C}, V_{\text{R}} = 600\text{ V}$	Q_{r}	-	1,8	-	μAs
Abschaltenergie pro Puls reverse recovery energy	$I_{\text{F}}=I_{\text{Nenn}}, -di_{\text{F}}/dt = 400\text{ A}/\mu\text{s}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 25^\circ\text{C}, V_{\text{R}} = 600\text{ V}$ $V_{\text{GE}} = -10\text{V}, T_{\text{vj}} = 125^\circ\text{C}, V_{\text{R}} = 600\text{ V}$	E_{RO}	-	0,55	-	mWs
			-	1,1	-	mWs
Transistor Brems-Chopper/ Transistor Brake-Chopper			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{\text{GE}} = 15\text{V}, T_{\text{vj}} = 25^\circ\text{C}, I_{\text{C}} = 10\text{ A}$ $V_{\text{GE}} = 15\text{V}, T_{\text{vj}} = 125^\circ\text{C}, I_{\text{C}} = 10\text{ A}$	$V_{\text{CE sat}}$	-	1,85	2,5	V
Gate-Schwellenspannung gate threshold voltage	$V_{\text{CE}} = V_{\text{GE}}, T_{\text{vj}} = 25^\circ\text{C}, I_{\text{C}} = 0,3\text{ mA}$	$V_{\text{GE(TO)}}$	5,0	5,8	6,5	V
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{\text{vj}} = 25^\circ\text{C}$ $V_{\text{CE}} = 25\text{ V}, V_{\text{GE}} = 0\text{ V}$	C_{ies}	-	0,6	-	nF
Kollektor-Emitter Reststrom collector-emitter cut off current	$V_{\text{GE}} = 0\text{V}, T_{\text{vj}} = 25^\circ\text{C}, V_{\text{CE}} = 1200\text{ V}$	I_{CES}	-	5,0	-	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{\text{CE}} = 0\text{V}, V_{\text{GE}} = 20\text{V}, T_{\text{vj}} = 25^\circ\text{C}$	I_{GES}	-	-	400	nA
Schaltverluste und -bedingungen Switching losses and conditions	siehe Wechselrichter in Dbl FP10R12KE3 see inverter in datasheet FP10R12KE3					
Diode Brems-Chopper/ Diode Brake-Chopper			min.	typ.	max.	
Durchlaßspannung forward voltage	$T_{\text{vj}} = 25^\circ\text{C}, I_{\text{F}} = 10\text{ A}$ $T_{\text{vj}} = 125^\circ\text{C}, I_{\text{F}} = 10\text{ A}$	V_{F}	-	1,8	2,5	V
Schaltverluste und -bedingungen Switching losses and conditions	siehe Wechselrichter in Dbl FB10R12KE3 see inverter in datasheet FB10R12KE3					
NTC-Widerstand/ NTC-Thermistor			min.	typ.	max.	
Nennwiderstand rated resistance	$T_C = 25^\circ\text{C}$	R_{25}	-	5	-	kΩ
Abweichung von R_{100} deviation of R_{100}	$T_C = 100^\circ\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung power dissipation	$T_C = 25^\circ\text{C}$	P_{25}			20	mW
B-Wert B-value	$R_2 = R_1 \exp [B(1/T_2 - 1/T_1)]$	$B_{25/50}$		3375		K

Technische Information / Technical Information

IGBT-Module
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Vorläufige Daten Preliminary data

Thermische Eigenschaften / Thermal properties

		min.	typ.	max.		
Innerer Wärmewiderstand thermal resistance, junction to case	Gleicher. Diode/ Rectif. Diode	R_{thJC}	-	-	1	K/W
	Trans. Wechr./ Trans. Inverter		-	-	1,2	K/W
	Diode Wechr./ Diode Inverter		-	-	1,5	K/W
	Trans. Bremse/ Trans. Brake		-	-	1,5	K/W
	Diode Bremse/ Diode Brake		-	-	2,3	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Gleicher. Diode/ Rectif. Diode	R_{thCK}	-	0,08	-	K/W
	Trans. Wechr./ Trans. Inverter	$\lambda_{paste}=1W/m^2K$	-	0,04	-	K/W
	Diode Wechr./ Diode Inverter	$\lambda_{grease}=1W/m^2K$	-	0,08	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature		T_{op}	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

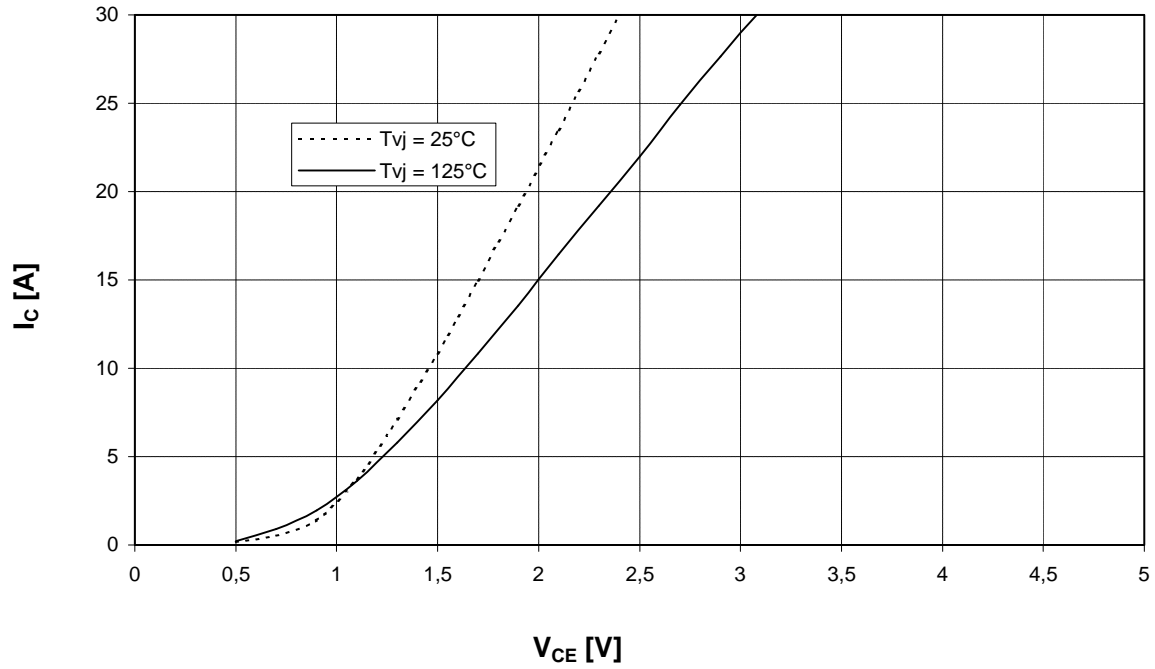
Innere Isolation internal insulation				Al_2O_3	
CTI comperative tracking index				225	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M		3 $\pm 10\%$	Nm
Gewicht weight		G		180	g



Vorläufige Daten
Preliminary data

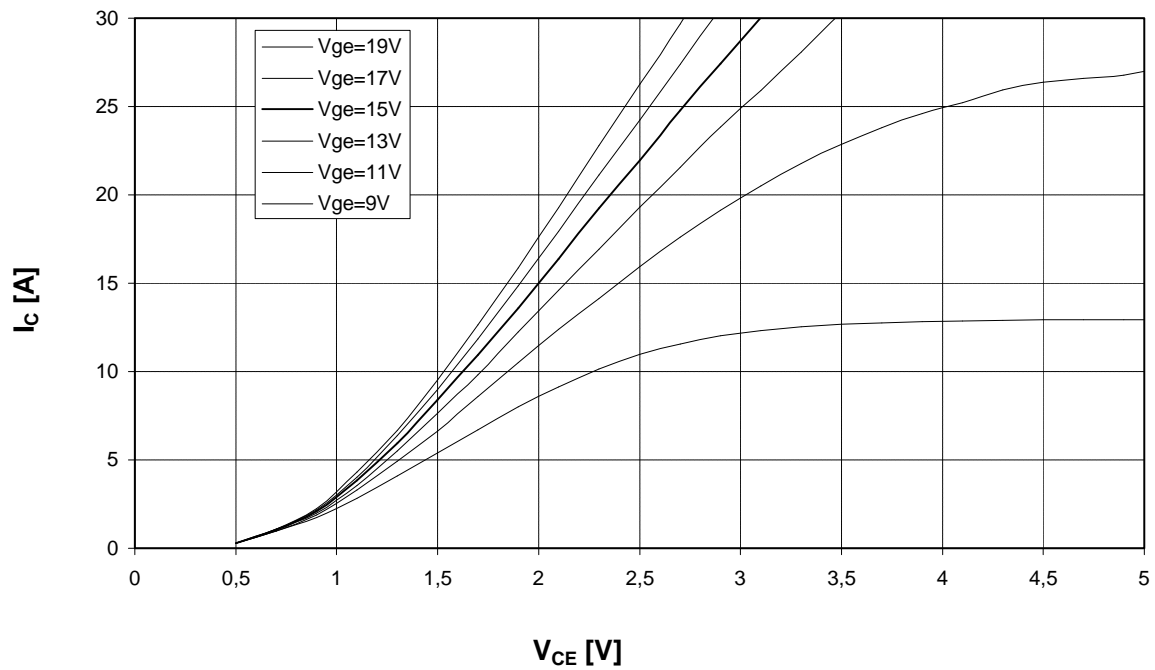
Ausgangskennlinienfeld Wechselr. (typisch)
Output characteristic Inverter (typical)

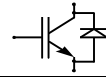
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



Ausgangskennlinienfeld Wechselr. (typisch)
Output characteristic Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$

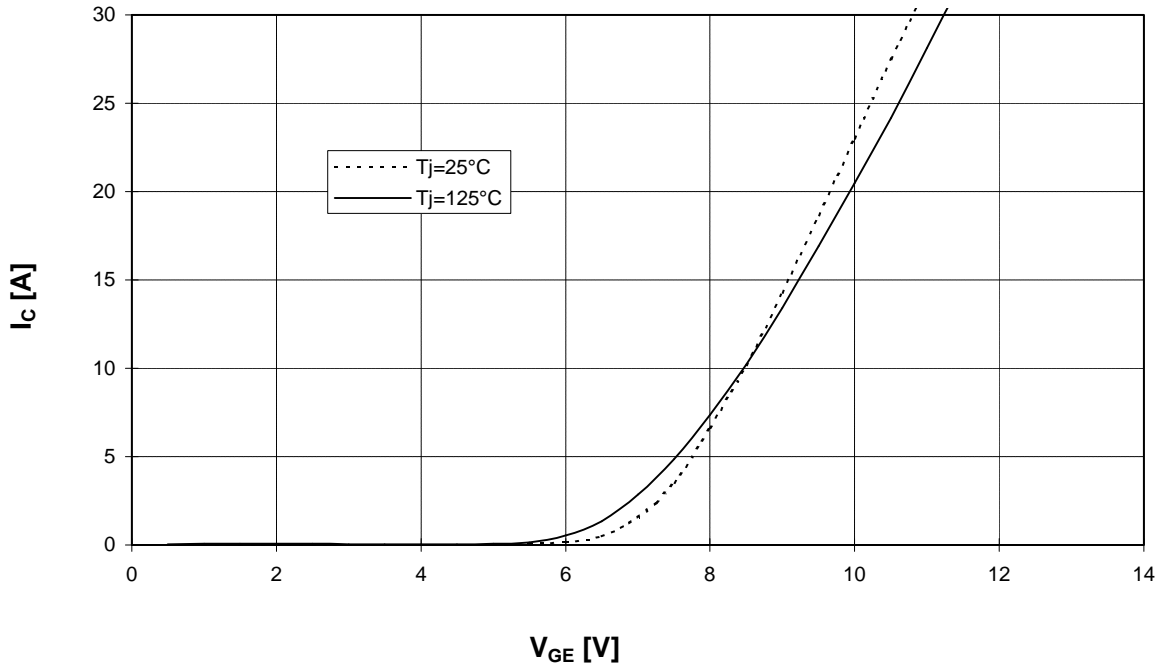




Vorläufige Daten
Preliminary data

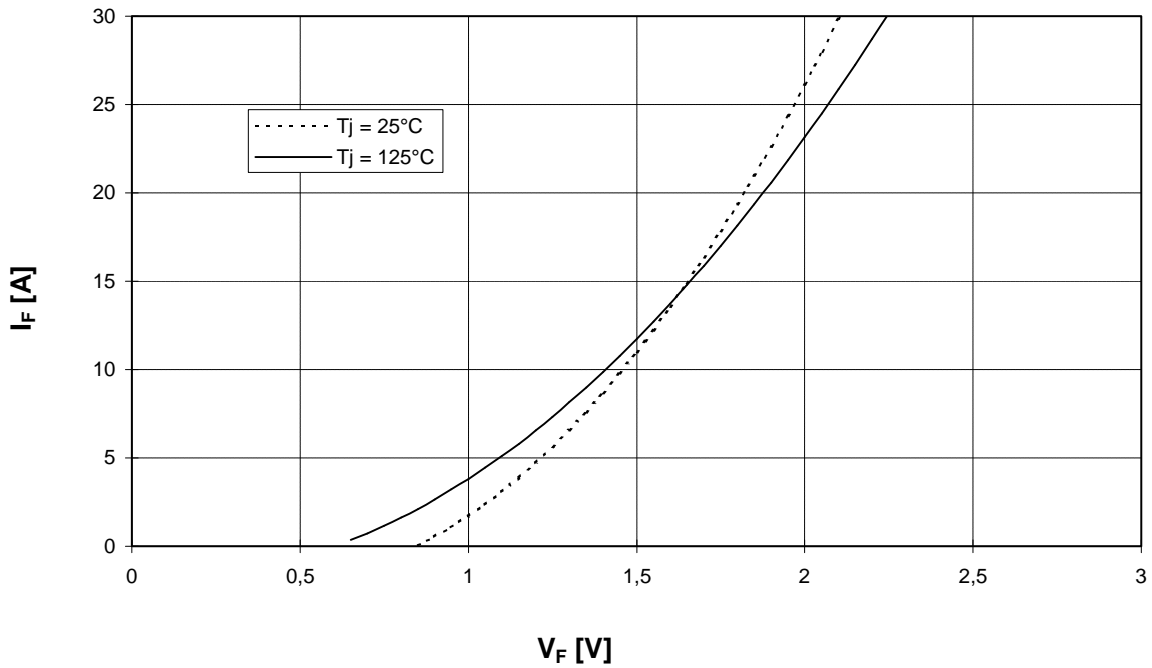
Übertragungscharakteristik Wechselr. (typisch)
Transfer characteristic Inverter (typical)

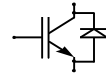
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Durchlaßkennlinie der Freilaufdiode Wechselr. (typisch)
Forward characteristic of FWD Inverter (typical)

$I_F = f(V_F)$

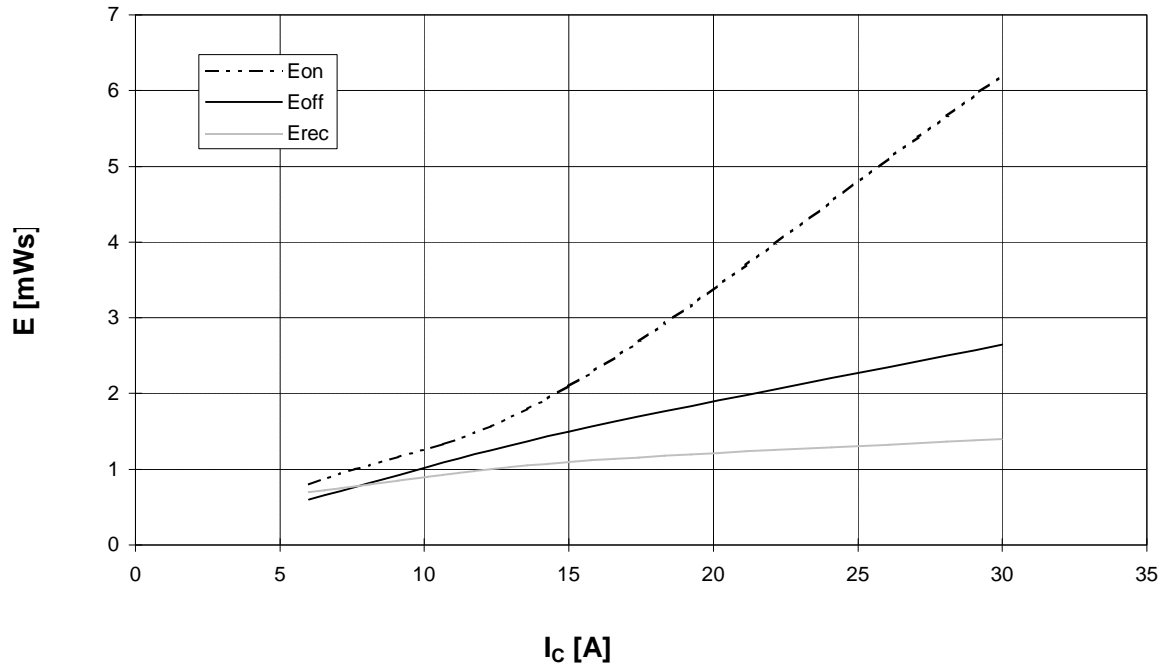




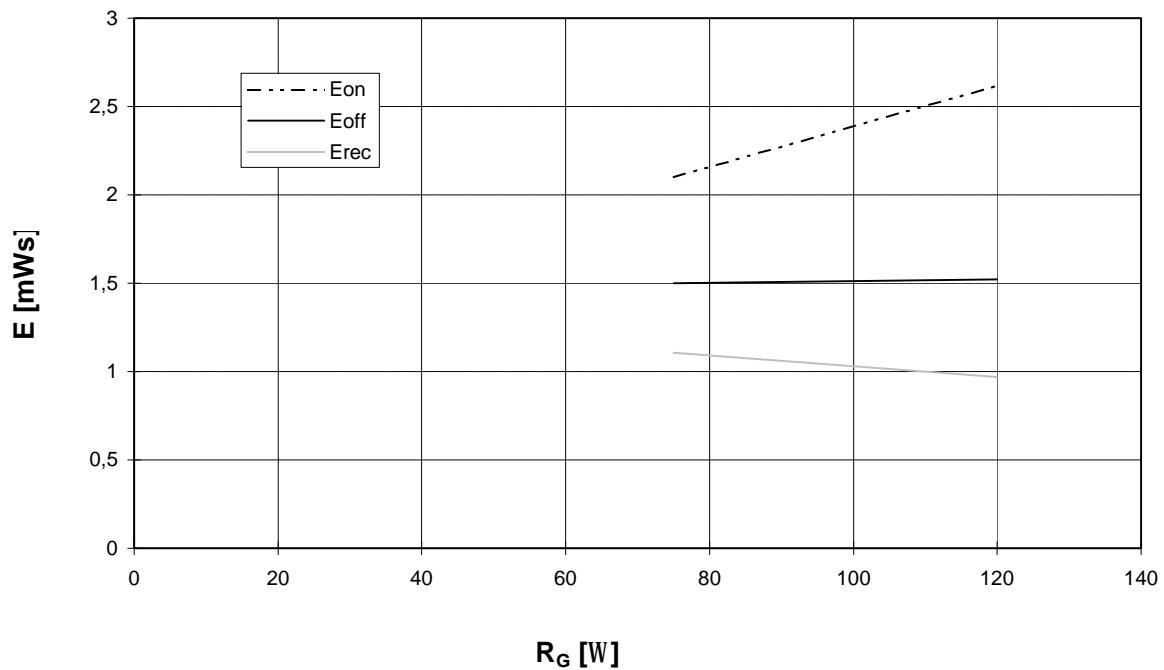
Vorläufige Daten

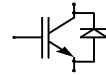
Preliminary data

Schaltverluste Wechselr. (typisch) $E_{on} = f(I_C), E_{off} = f(I_C), E_{rec} = f(I_C)$ $V_{CC} = 600\text{ V}$
 Switching losses Inverter (typical) $T_j = 125^\circ\text{C}, V_{GE} = \pm 15\text{ V}, R_{Gon} = R_{Goff} = 75\text{ Ohm}$



Schaltverluste Wechselr. (typisch) $E_{on} = f(R_G), E_{off} = f(R_G), E_{rec} = f(R_G)$
 Switching losses Inverter (typical) $T_j = 125^\circ\text{C}, V_{GE} = \pm 15\text{ V}, I_C = I_{nenn}, V_{CC} = 600\text{ V}$

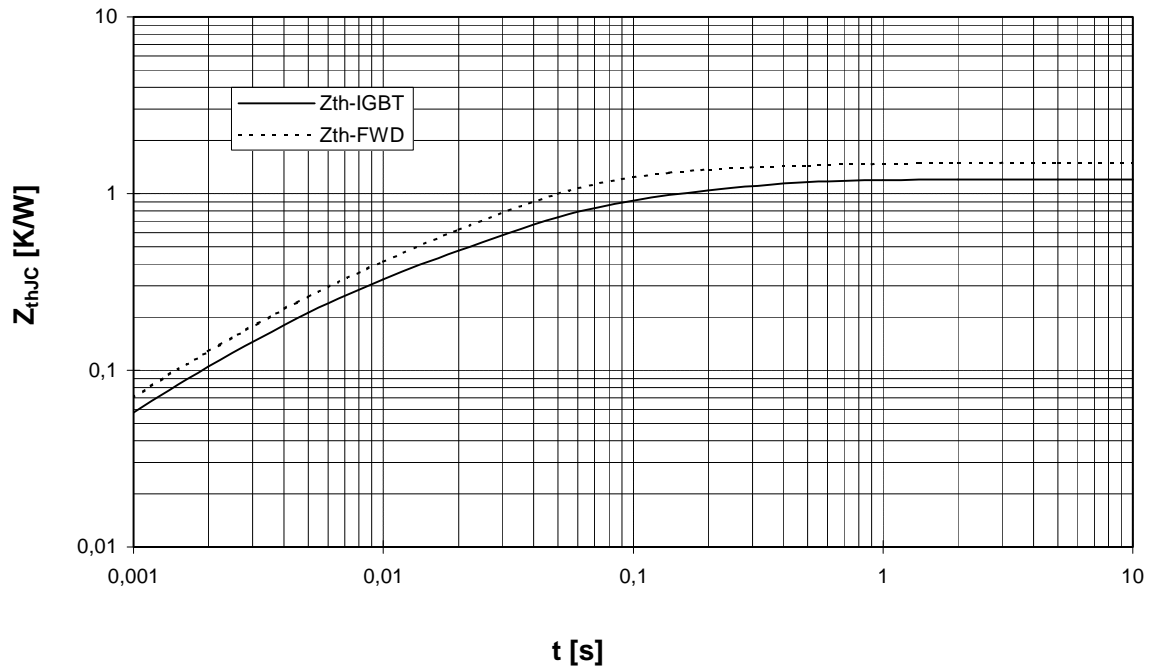




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Transienter Wärmewiderstand Wechsler.
Transient thermal impedance Inverter

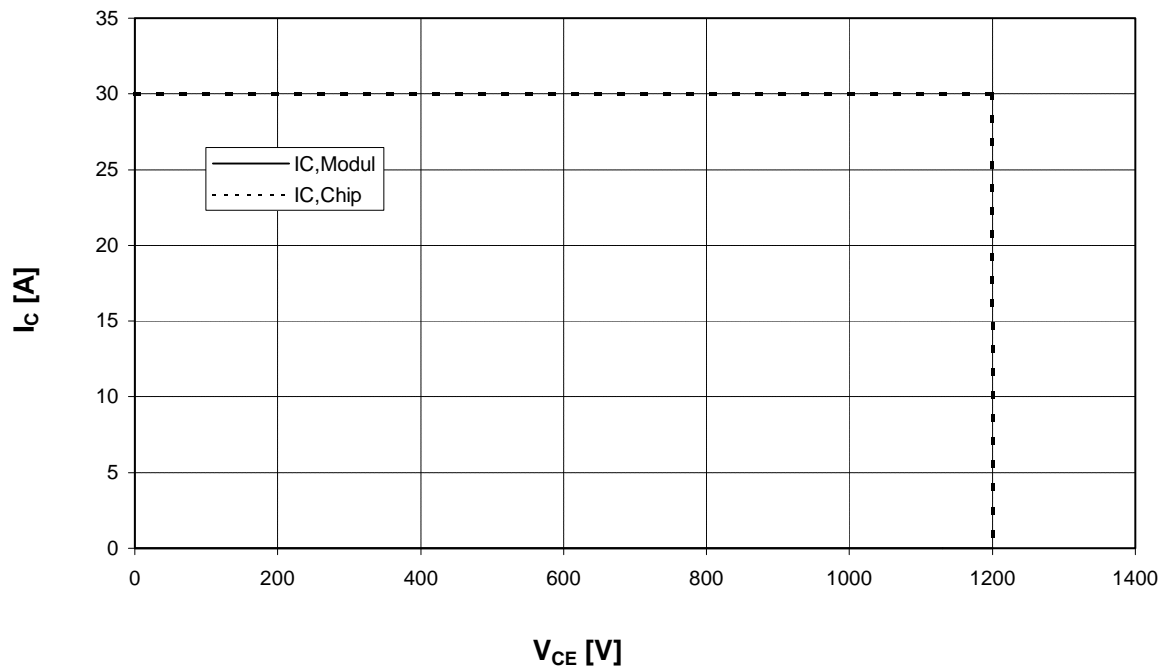
$$Z_{thJC} = f(t)$$

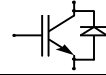


Sicherer Arbeitsbereich Wechsler. (RBSOA)

$$I_C = f(V_{CE})$$

Reverse bias safe operating area Inverter (RBSOA) $T_{vj} = 125^\circ\text{C}$, $V_{GE} = \pm 15\text{V}$





Vorläufige Daten

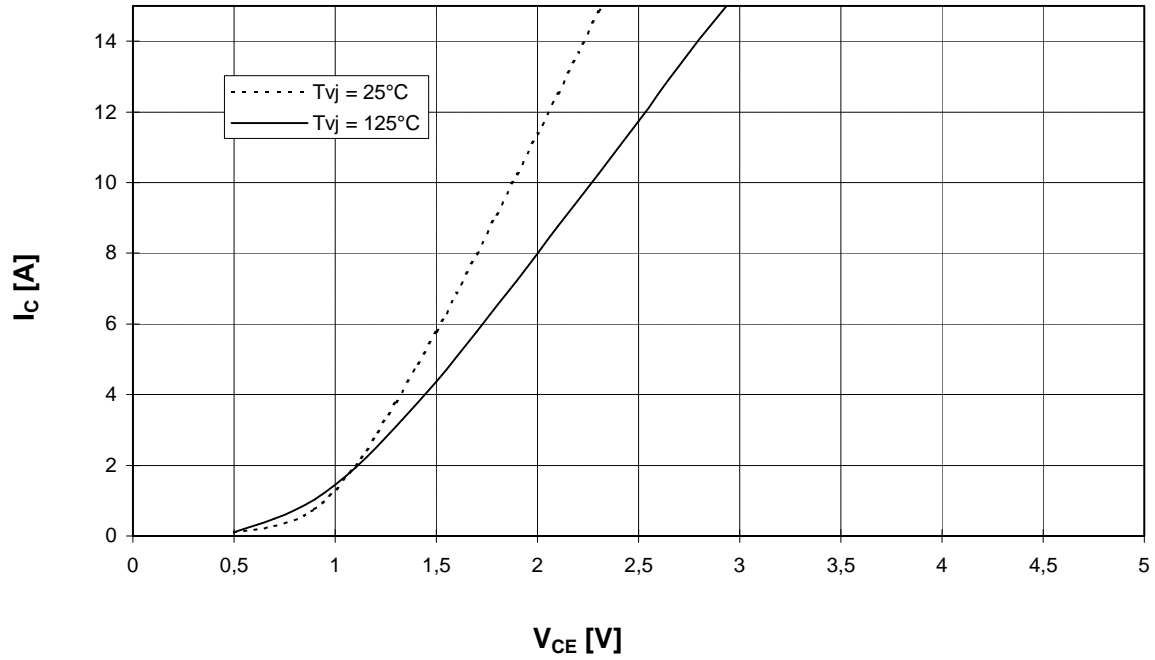
Preliminary data

Ausgangskennlinienfeld Brems-Chopper-IGBT (typisch)

Output characteristic brake-chopper-IGBT (typical)

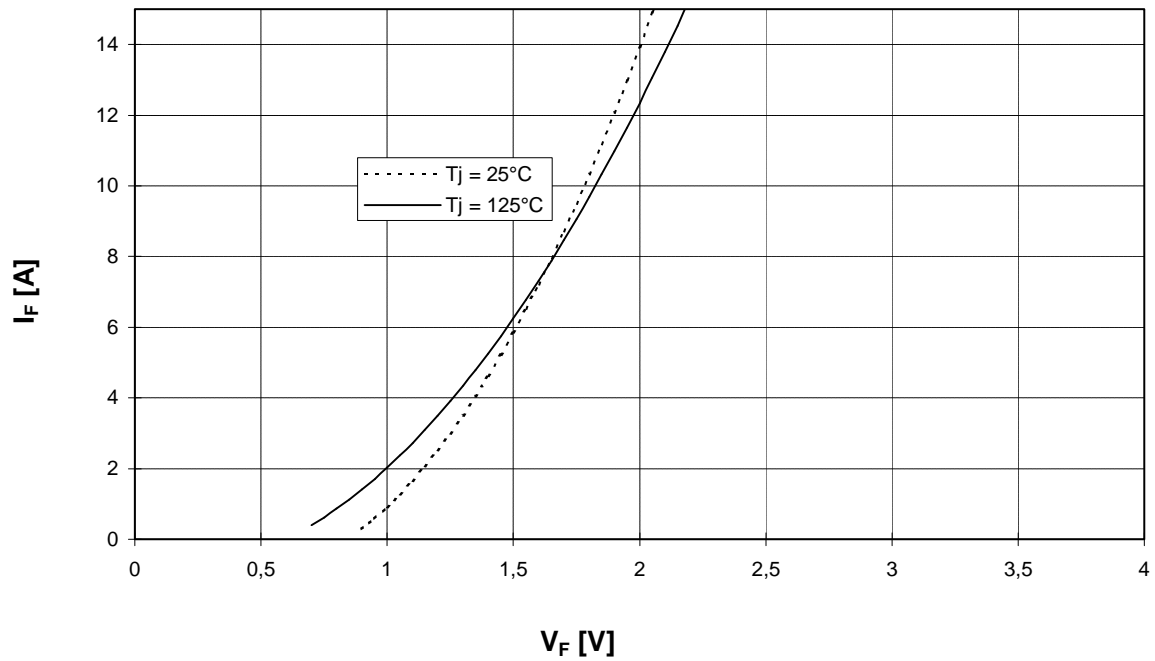
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



Durchlaßkennlinie der Brems-Chopper-Diode (typisch) $I_F = f(V_F)$

Forward characteristic of brake-chopper-FWD (typical)

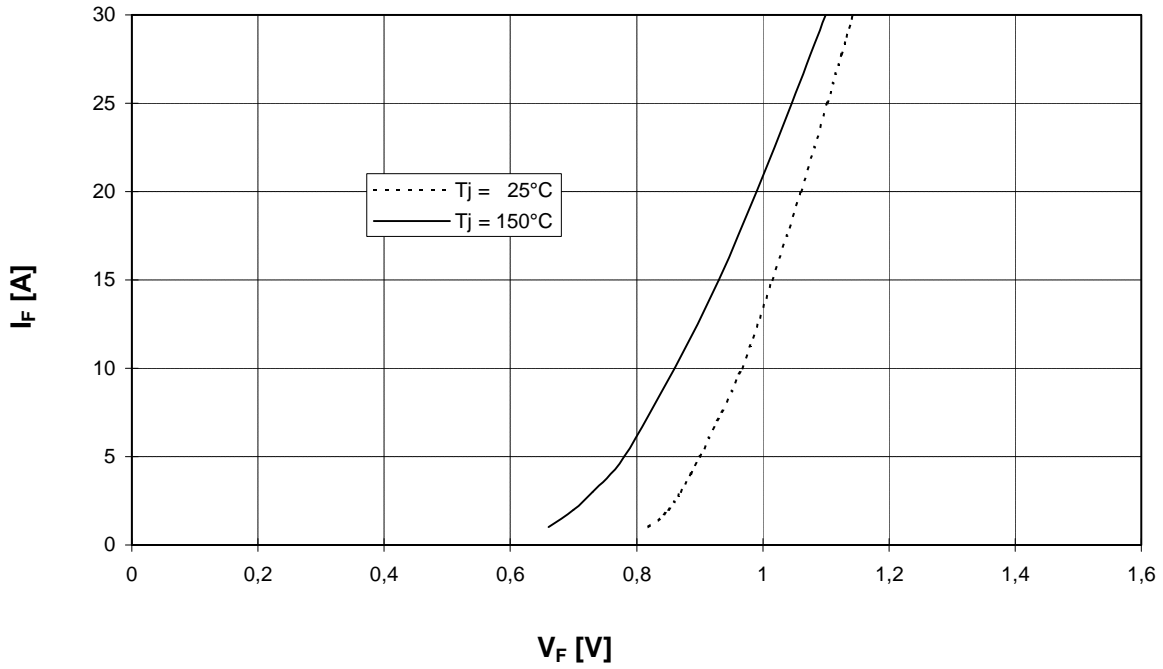




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Durchlaßkennlinie der Gleichrichterdiode (typisch)
Forward characteristic of Rectifier Diode (typical)

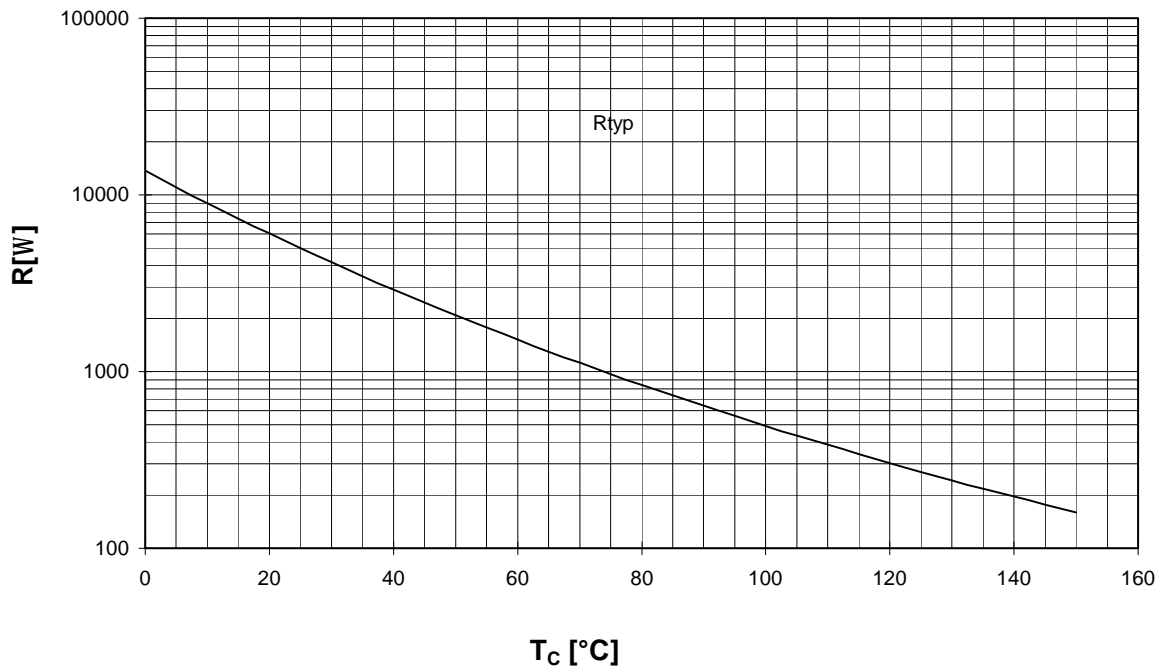
$$I_F = f(V_F)$$

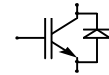


NTC- Temperaturkennlinie (typisch)

$$R = f(T)$$

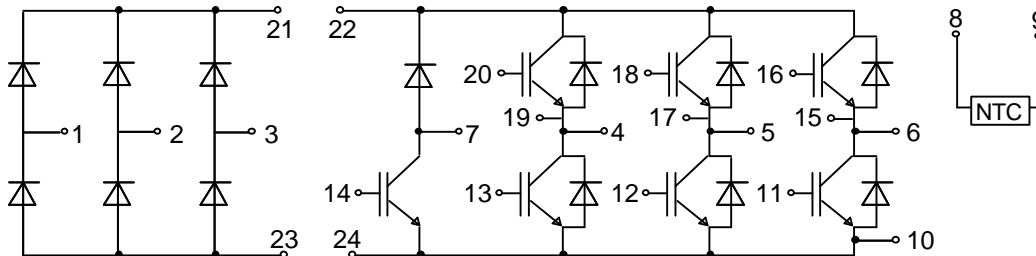
NTC- temperature characteristic (typical)



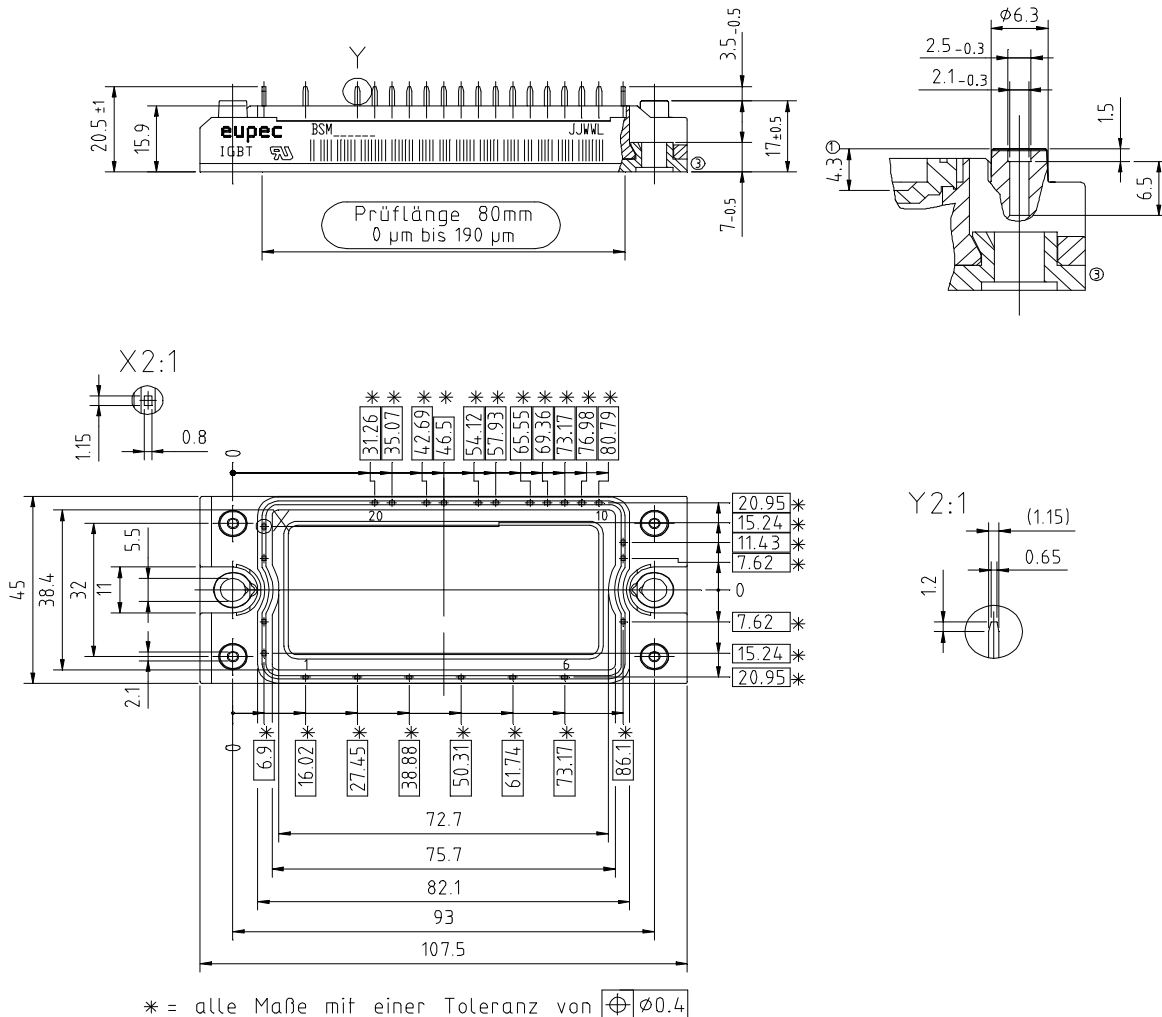


Vorläufige Daten
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Schaltplan/ Circuit diagram



Gehäuseabmessungen/ Package outlines



Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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